

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	37881	(high near dielectric)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	625	(high near dielectric) near (insulat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	4	((high near dielectric) near (insulat\$3)) near35 (crystal defect)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	20	((high near dielectric) near (insulat\$3)) same (crystal defect)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
5	BRS	L5	11	((dielectric) near (insulat\$3)) same (crystal near defect)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	426	((dielectric)) same (crystal near defect)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	4	((dielectric)) same (irradiat\$3 near5 crystal near defect)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	7379	((dielectric)) same (irradiat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
9	BRS	L9	243	((high near dielectric)) same (irradiat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	6	((high near dielectric) near25 (silicon)) same (irradiat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	44	((high near dielectric) near25 (silicon)) same (radiat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	3826	((high near dielectric) near25 (silicon))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Type	L #	Hits	Search Text	DBs
13	BRS	L13	196	((high near dielectric) near25 (silicon)) same (crystal or monocrystal\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	590	((high near dielectric) near25 (silicon)) same (reduc\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	13	((high near dielectric) near25 (silicon)) same ((reduc\$3) near25 (crystal or defect\$1))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	50	((high near dielectric) near25 (silicon)) same (irradiat\$3 or radiat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B